MOSFETs Silicon P-Channel MOS (U-MOSVI)

# **TPCP8105**

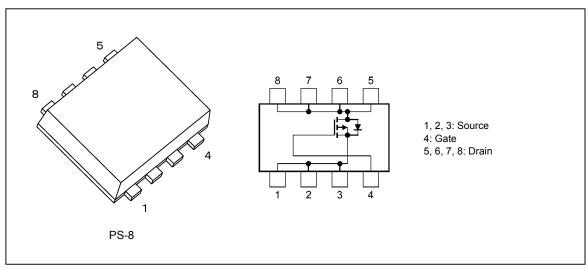
#### 1. Applications

- Lithium-Ion Secondary Batteries
- Power Management Switches
- Notebook PCs

#### 2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 13.8 \text{ m}\Omega \text{ (typ.)} (V_{GS} = -4.5 \text{ V})$
- (3) Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -20 \ V)$
- (4) Enhancement mode:  $V_{th}$  = -0.5 to -1.2 V ( $V_{DS}$  = -10 V,  $I_D$  = -1 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	-20	V
Gate-source voltage			V <sub>GSS</sub>	±12	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	-7.2	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	-28.8	
Power dissipation	(t = 5 s)	(Note 2)	PD	1.68	W
Power dissipation	(t = 5 s)	(Note 3)	PD	0.84	W
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	33.0	mJ
Avalanche current			I <sub>AR</sub>	-7.2	А
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

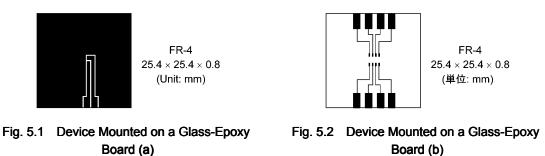
Characteristic	Symbol	Max	Unit		
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R <sub>th(ch-a)</sub>	74.4	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)	R <sub>th(ch-a)</sub>	148.8	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V<sub>DD</sub> = -16 V, T<sub>ch</sub> = 25°C (initial), L = 0.5 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = -7.2 A



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

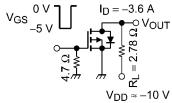
#### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±12 V, $V_{DS}$ = 0 V	_	—	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	$V_{DS}$ = -20 V, $V_{GS}$ = 0 V	—	_	-10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-20	_	_	V
Drain-source breakdown voltage (Note 5)	V <sub>(BR)DSX</sub>	$I_{D}$ = -10 mA, $V_{GS}$ = 8 V	-12	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.5	—	-1.2	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1.8 A		28	60	mΩ
		V <sub>GS</sub> = -2.0 V, I <sub>D</sub> = -1.8 A	—	25	45	
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -3.6 A	_	17.9	23	
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.6 A	—	13.8	17	

Note 5: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	—	2280	—	pF
Reverse transfer capacitance	C <sub>rss</sub>		—	296	_	
Output capacitance	C <sub>oss</sub>		—	340	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	—	7.2	_	ns
Switching time (turn-on time)	t <sub>on</sub>		—	15	_	
Switching time (fall time)	t <sub>f</sub>		—	71	_	
Switching time (turn-off time)	t <sub>off</sub>		_	241	_	



Duty  $\leq~$  1%,  $t_W = 10~\mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx$ -16 V, $V_{GS}$ = -5 V, $I_D$ = -7.2A	—	28	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	5	_	
Gate-drain charge	Q <sub>gd</sub>		-	7	-	

#### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I <sub>DRP</sub>	—	—	—	-28.8	А
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = -7.2 A, V <sub>GS</sub> = 0 V			1.2	V

Note 6: Ensure that the channel temperature does not exceed 150°C.

7. Marking

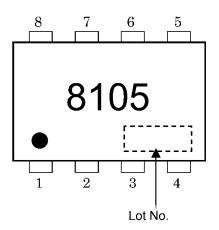


Fig. 7.1 Marking

1.5

1.4

1.3

-12

160

#### 8. Characteristics Curves (Note)

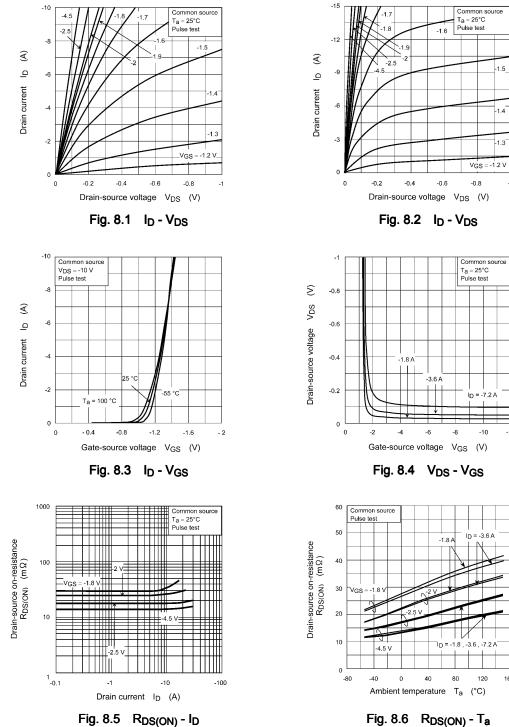
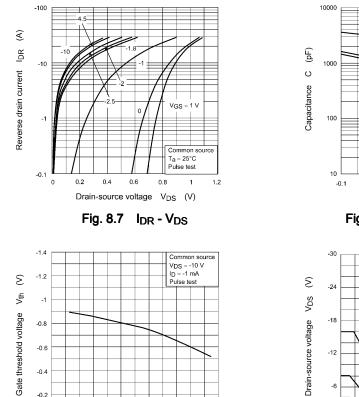


Fig. 8.6 RDS(ON) - Ta



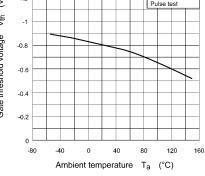
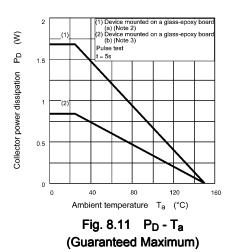


Fig. 8.9 Vth - Ta



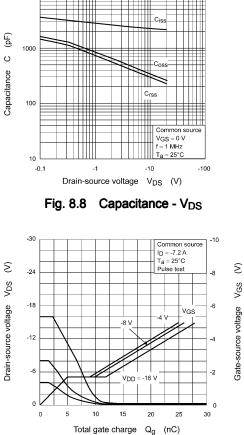


Fig. 8.10 Dynamic Input/Output Characteristics

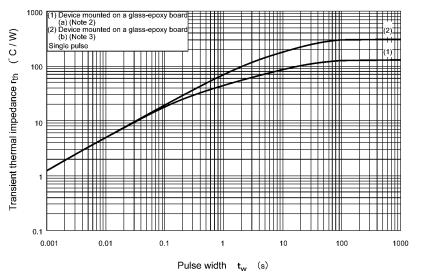
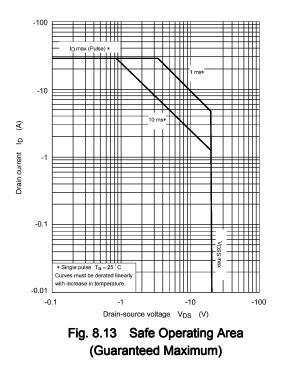


Fig. 8.12 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

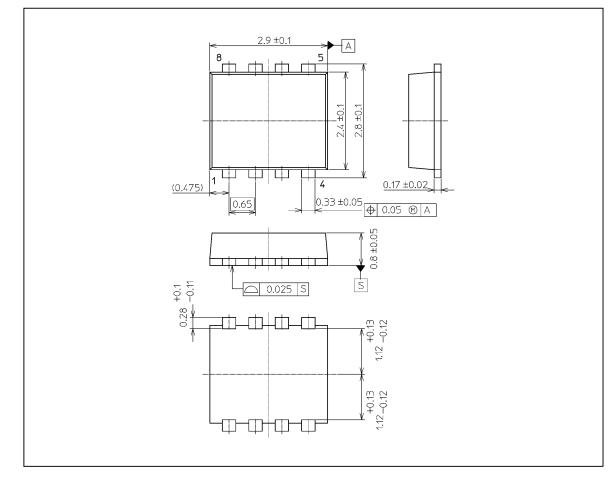


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

#### **TPCP8105**

#### **Package Dimensions**

Unit: mm



#### Weight: 0.017 g (typ.)

Package Name(s) TOSHIBA: 2-3V1S Nickname: PS-8

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